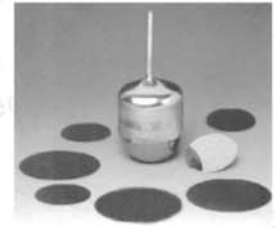


GaAs Single Crystal (ingot, polished wafer)



Type	Dopant	Orientation	Diameter mm	Consistency cm^{-3}	Resistivity $\Omega \text{ cm}$	Mobility cm^2/Vs	Dislocation Density $1/\text{cm}^2$
LEC-50	—	<100>	$\Phi 50.8$	—	$\geq 1 \times 10^7$	≥ 5000	≤ 50000
LEC-50Cr	Cr						
LEC-76	—	<100>	$\Phi 76.2$	—	$\geq 1 \times 10^7$	≥ 5000	≤ 50000
LEC-76Cr	Cr						
LEC-76Si	Si	<100>	$\Phi 76.2$	$\geq 1 \times 10^{18}$	—	≥ 1500	≤ 10000
LEC-76Cr	Cr			$\geq (5-40) \times 10^{17}$			
HB-50Si	Si	<100>	$\Phi 50.8$	$\geq 1 \times 10^{18}$	—	≥ 1300	≤ 1000
HB-50Cr	Cr			—			
Applications	Ultra high speed IC , gate array micro wave device ,photoelectric device etc						

